## Supporting Information

## Multifunctional black phosphorus pressure sensors with bending angle and

## direction recognition characteristics

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**Figure S11** The sensing curves of handwriting process with numbers 0-9 (a, b) and English letters A-Z (c, d, e and f). The handwriting process is performed by volunteer.

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Figure S15 Photograph of our home-made Cu<sub>2</sub>ZnSn(S,Se)<sub>4</sub> thin film solar cell arrays.

**Figure S16** Current density-voltage (J-V) characteristics of the solar cell based on  $Cu_2ZnSn(S,Se)_4$  under calibrated AM 1.5G illumination generated by an AAA-class solar simulator (Oriel Sol3A 94023A, from Newport), current-voltage (I-V) curves were recorded on a Keithley 4200-SCS semiconductor measurement system.



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